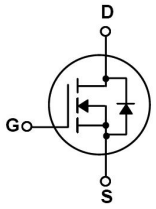
/ Descriptions

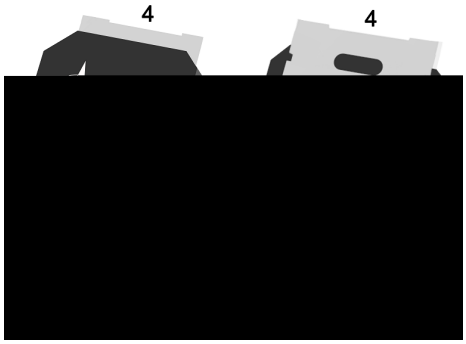
TO-252 ĻĻĿ N ॐ MOS ʃ ѽ Ẓ ٦
N-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Features

V_{DS}(V) = 20V I_D=65A(V_{GS} = 12V)
$R_{DS(ON)}$@4.5V 8mƑ(Typ. 5mƑ)
$R_{DS(ON)}$@2.5V 10mƑ(Typ. 6.2mƑ)
ɳ ғ β HF Product.

ॾ ৯ ı ' GF2GF ॼ Ω ⊐ ı ' Ầ ԋ
These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.





PIN1 χ G PIN 2 χ D PIN 3 χ S PIN 4 χ D

/ Marking

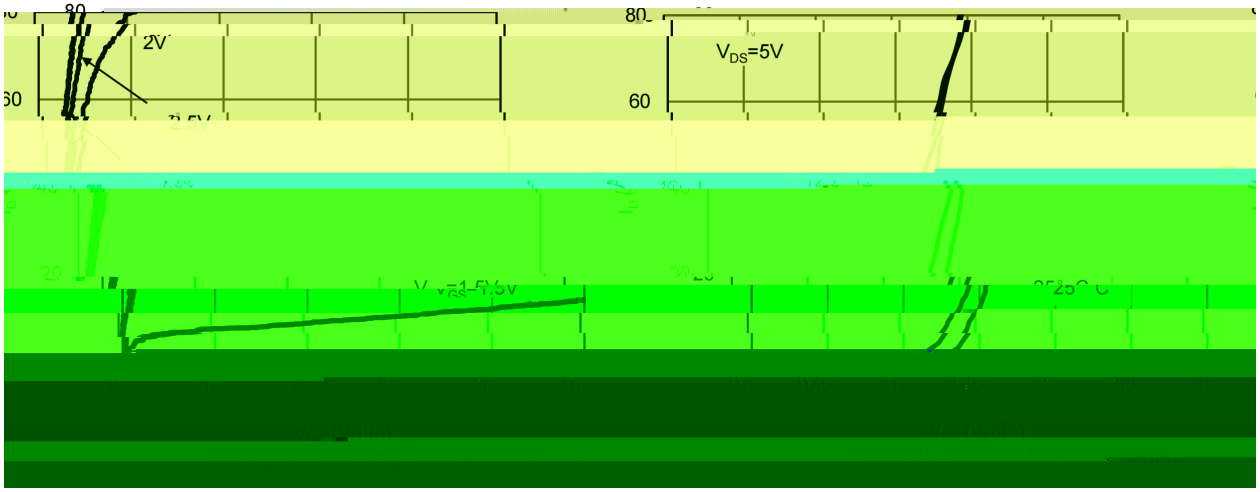
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See Marking Instructions.

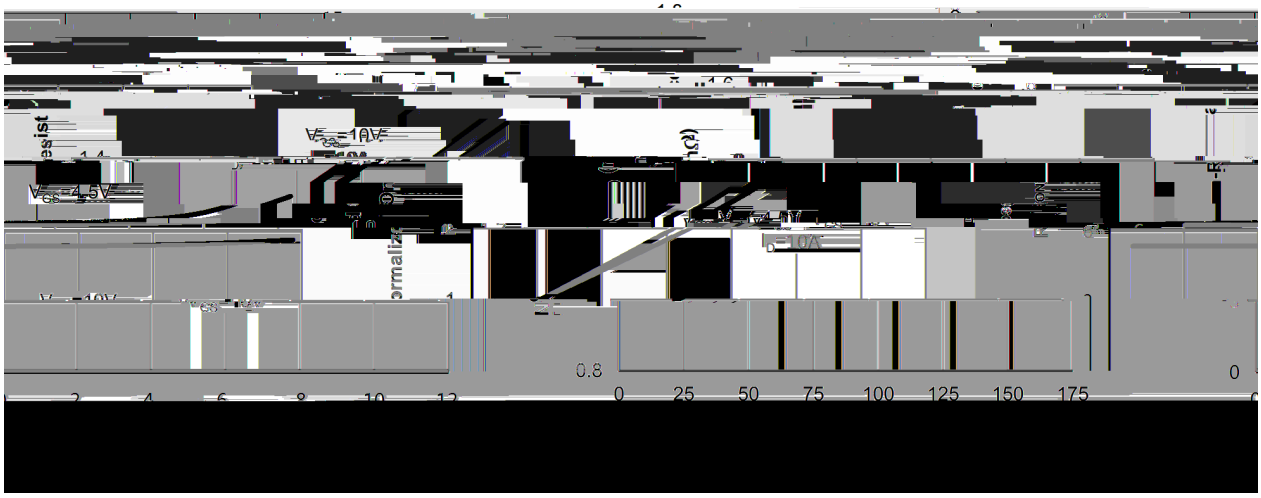
v ¨Ω Parameter		ϒ N Symbol	¨Ω Ö Rating	D Ч Unit
Drain-Source Voltage		V_{DSS}	20	V
Drain Current		I_D(Tc=25)	65	A
Peak Drain Current		I_{DM}	157	A
Gate-Source Voltage		V_{GSS}	12	V
Avalanche Current		I_{AS}	19	A
Single Pulsed Avalanche Energy		E_{AS}	361	mJ
Total Power Dissipation		P_D(Tc=25)	52	W
Junction and Storage Temperature Range		T_J,T_{STG}	-55 to 150	
Thermal resistance, junction - ambient	t 10s	$R_{\theta JA}$	20	/W
	Steady-State		50	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	1.55	

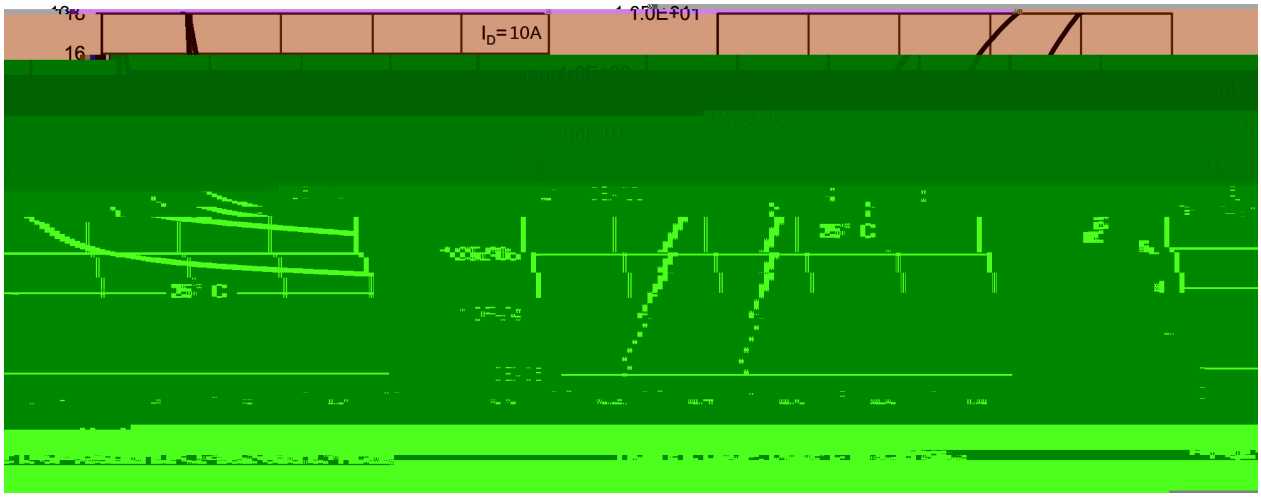
v ¨Ω Parameter	ϒ N Symbol	╨ :┆ ┳ Test Conditions	ϣ ϱ Ö Min	Ɛ ʒ Ö Typ	ϣ ᶻ Ö Max	D Ч Unit

v ˝Ω Parameter	ϒ N Symbol	╜ ;ϯ ţ Test Conditions	ѡ ņ Ө Min	Ɛ ʒ Ө Typ	ѡ ᶻ Ө Max	ɒ Ꮒ Unit
Total Gate Charge	Q_g	V_{GS}=4.5V, V_{DS}=10V, I_D=18A		14.7		nC
Gate Source Charge	Q_{gs}			1.9		
Gate Drain Charge	Q_{gd}			4.7		
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=4.5V V_{DS}=10V R_L=0.75Ω R_{GEN}=3Ω		13		ns
Turn-On Rise Time	t_r			23		ns
Turn-Off Delay Time	$t_{d(of}$					

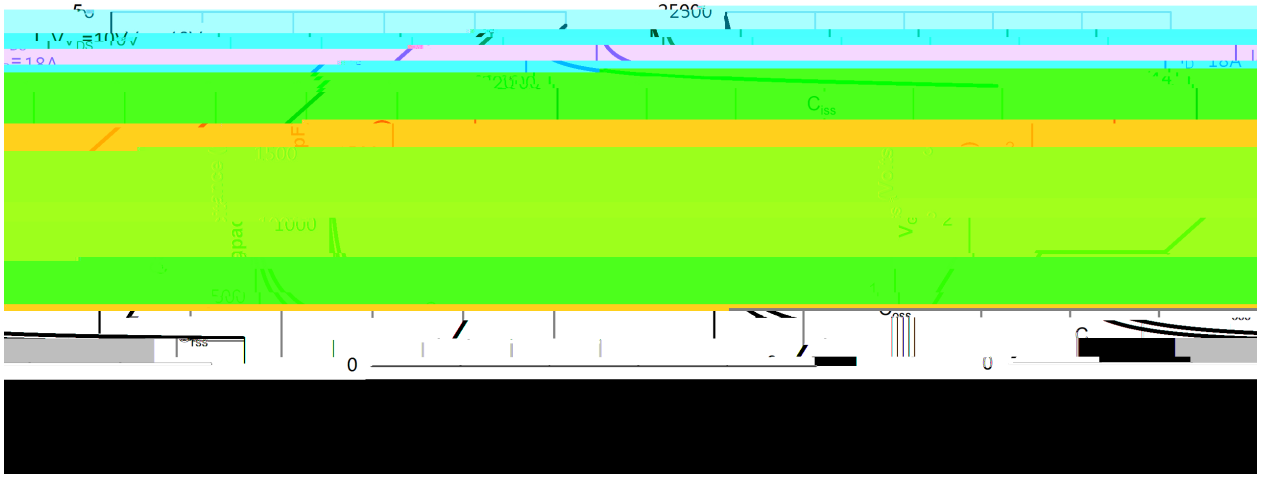
/ Electrical Characteristic Curve



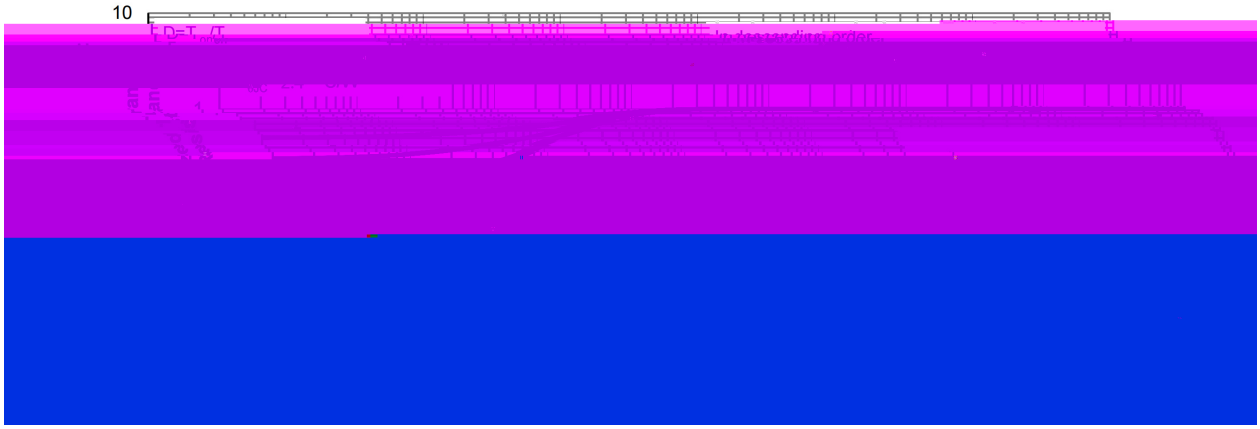




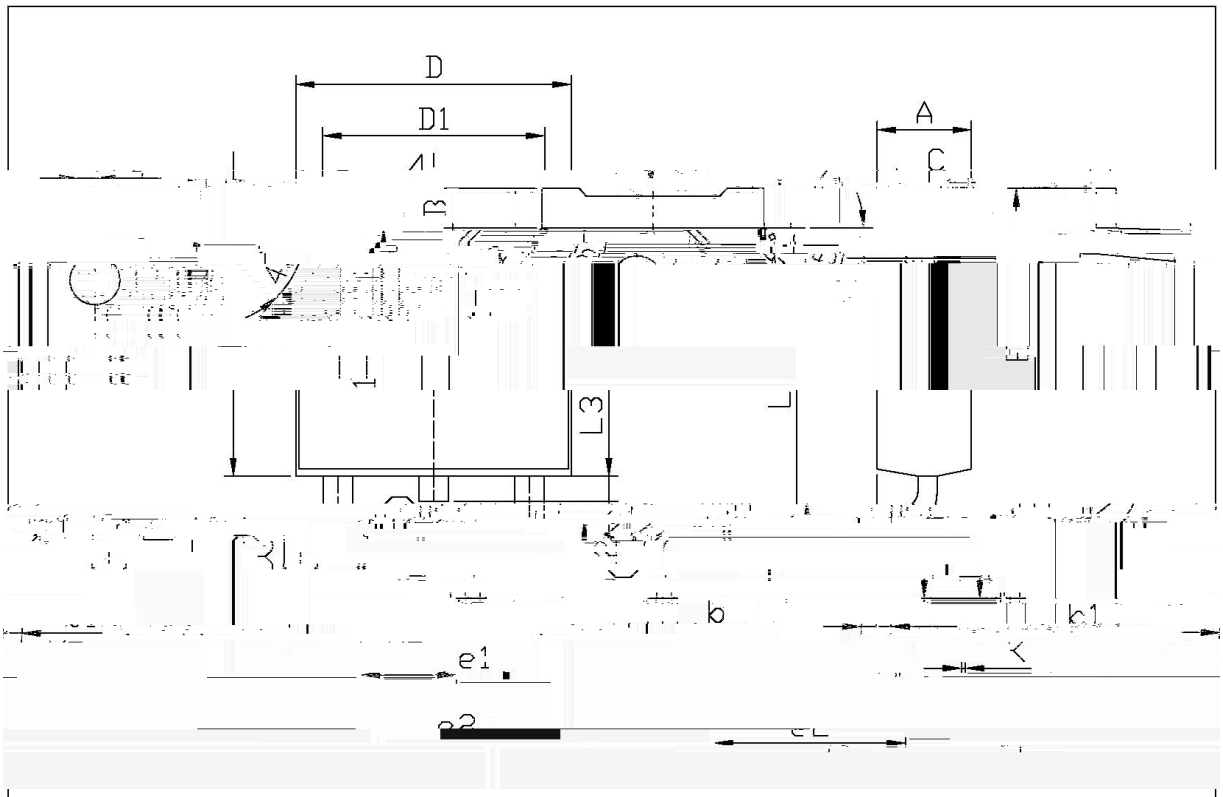
/ Electrical Characteristic Curve







/ Package Dimensions



单位：mm

Symbol	Min	Max	Symbol	Min	Max
e1	2.24	2.32	B	0.95	1.25
K	0.00	0.10	D1	5.10	5.50

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